

V K Dixit

List of Publications by Year in descending order

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31
papers

324
citations

840776

11
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888059

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docs citations

31
times ranked

381
citing authors

#	ARTICLE	IF	CITATIONS
1	Influence of interface states on built-in electric field and diamagnetic-Landau energy shifts in asymmetric modulation-doped InGaAs/GaAs QWs. Journal Physics D: Applied Physics, 2022, 55, 385101.	2.8	1
2	Effect of germanium auto-diffusion on the bond lengths of Ga and P atoms in GaP/Ge(111) investigated by using X-ray absorption spectroscopy. Journal of Synchrotron Radiation, 2021, 28, 480-489.	2.4	0
3	Electric and magnetic field effects on the exciton localization in a modulation doped InGaAs/GaAs quantum well. AIP Conference Proceedings, 2020, , .	0.4	1
4	Simultaneous magneto-electro-optical measurements in modulation-doped quantum well: An investigation on magneto-photoluminescence intensity oscillations. Journal of Applied Physics, 2019, 125, 205701.	2.5	1
5	Radiative and non-radiative recombination of thermally activated magneto-excitons probed via quasi-simultaneous photoluminescence and surface-photovoltage spectroscopy. Journal of Applied Physics, 2018, 124, .	2.5	5
6	Effect of disorders on the optical properties of excitons in InAsP/InP quantum wells investigated by magneto-photoluminescence spectroscopy. Journal of the Optical Society of America B: Optical Physics, 2018, 35, 2405.	2.1	7
7	The effect of magnetic field on free and bound exciton luminescence in GaAs/AlGaAs multiple quantum well structures: a quantitative study on the estimation of ultra-low disorder. Journal Physics D: Applied Physics, 2017, 50, 335107.	2.8	6
8	Effect of carrier confinement on effective mass of excitons and estimation of ultralow disorder in Al _x Ga _{1-x} As/GaAs quantum wells by magneto-photoluminescence. Scientific Reports, 2017, 7, 4905.	3.3	24
9	Observation of anisotropic distribution of microstructure in GaP/GaAs epitaxial layers. Journal of Applied Physics, 2016, 120, .	2.5	6
10	Charge carrier localization effects on the quantum efficiency and operating temperature range of InAs _x P _{1-x} /InP quantum well detectors. Journal of Applied Physics, 2016, 119, .	2.5	10
11	Development and application of InAsP/InP quantum well infrared detector. AIP Conference Proceedings, 2016, , .	0.4	0
12	Study of the microstructure information of GaAs epilayers grown on silicon substrate using synchrotron radiation. Journal of Synchrotron Radiation, 2016, 23, 238-243.	2.4	3
13	Dislocation-assisted tunnelling of charge carriers across the Schottky barrier on the hydride vapour phase epitaxy grown GaN. Journal of Applied Physics, 2015, 118, .	2.5	21
14	Dislocations limited electronic transport in hydride vapour phase epitaxy grown GaN templates: A word of caution for the epitaxial growers. Applied Physics Letters, 2015, 106, .	3.3	9
15	Investigation of crystalline and electronic band alignment properties of GaP/Ge(111) heterostructure. Applied Physics Letters, 2014, 104, .	3.3	16
16	Observation of room temperature optical absorption in InP/GaAs type-II ultrathin quantum wells and quantum dots. Journal of Applied Physics, 2014, 115, 223505.	2.5	1
17	A versatile phenomenological model for the S-shaped temperature dependence of photoluminescence energy for an accurate determination of the exciton localization energy in bulk and quantum well structures. Journal Physics D: Applied Physics, 2014, 47, 065103.	2.8	37
18	Temperature dependence of the photo-induced inverse spin Hall effect in Au/InP hybrid structures. Applied Physics Letters, 2014, 104, 042102.	3.3	11

#	ARTICLE	IF	CITATIONS
19	Low- and high-density InAs nanowires on Si(001) and their Raman imaging. Semiconductor Science and Technology, 2013, 28, 015025.	2.0	6
20	Evaluation of electronic transport properties and conduction band offsets of asymmetric InAs/In _x Ga _{1-x} As/GaAs dot-in-well structures. Journal Physics D: Applied Physics, 2012, 45, 365104.	2.8	6
21	Conduction band offset and quantum states probed by capacitance-voltage measurements for InP/GaAs type-II ultrathin quantum wells. Journal of Applied Physics, 2011, 109, .	2.5	7
22	Determination of band offsets in strained InAs _x P _{1-x} /InP quantum well by capacitance voltage profile and photoluminescence spectroscopy. Journal of Applied Physics, 2011, 109, .	2.5	10
23	Numerical simulation of inverse spin Hall spectra in Pt/GaAs hybrid structure. Journal Physics D: Applied Physics, 2011, 44, 265104.	2.8	10
24	Temperature dependence of the photoluminescence from InP/GaAs type-II ultrathin quantum wells. Journal Physics D: Applied Physics, 2010, 43, 455410.	2.8	9
25	Observation of electron confinement in InP/GaAs type-II ultrathin quantum wells. Applied Physics Letters, 2010, 97, .	3.3	22
26	Alloying induced degradation of the absorption edge of InAs _x Sb _{1-x} . Applied Physics Letters, 2007, 90, 101905.	3.3	20
27	Micro Raman and Photoluminescence Spectroscopy of Nano-Porous n and p Type GaN/Sapphire(0001). Journal of Nanoscience and Nanotechnology, 2007, 7, 2186-2191.	0.9	3
28	Studies on high resolution x-ray diffraction, optical and transport properties of InAs _x Sb _{1-x} GaAs (x=0.06) heterostructure grown using liquid phase epitaxy. Journal of Applied Physics, 2004, 96, 4989-4997.	2.5	23
29	Temperature dependence of the energy gap and free carrier absorption in bulk InAs _{0.05} Sb _{0.95} single crystals. Applied Physics Letters, 2003, 82, 4720-4722.	3.3	16
30	Structural, optical, and electrical properties of bulk single crystals of InAs _x Sb(1-x) grown by rotatory Bridgman method. Applied Physics Letters, 2002, 81, 1630-1632.	3.3	15
31	High-mobility InSb epitaxial films grown on a GaAs (001) substrate using liquid-phase epitaxy. Applied Physics Letters, 2002, 80, 2102-2104.	3.3	18